



<b>Session Title:</b>	<b>[WeB1] Power Device III</b>
<b>Session Date:</b>	<b>November 13 (Wed.), 2024</b>
<b>Session Time:</b>	<b>09:00-10:35</b>
<b>Session Room:</b>	<b>Room B (Grand Ballroom 1, 2F, Paradise Hotel Busan)</b>
<b>Session Chair:</b>	<b>Prof. Ho-Jun Lee (Pusan Nat'l Univ., Korea)</b>

**[WeB1-1] [Invited]**

**09:00-09:30**

**RISE Wide Bandgap Technology for System Integration: Research Activities and Facilities**

Jang-Kwon Lim, Jun-Ho Lee, Hithiksha Krishna Murthy, Saeed Akbari, Olof Öber, Magnus Lindberg, Qin Wang, Mietek Bakowski, Linda Johansson, and Klas Brinkfeldt (RISE Research Inst. of Sweden AB, Sweden)

**[WeB1-2] [Invited]**

**09:30-09:55**

**Current Status of  $\beta$ -Ga<sub>2</sub>O<sub>3</sub> Single Crystals by Edge-Defined Film-Fed Growth Method**

Si-Young Bae (Pukyong Nat'l Univ., Korea), Yun-Ji Shin, and Seong-Min Jeong (KICET, Korea)

**[WeB1-3]**

**09:55-10:15**

**Enhancement of GAA-FET by the Optimization of Channel Shape**

Min Kyun Sohn, Seong Hyun Lee, Sang-Hoon Kim, Jeong Woo Park, Wangjoo Lee, Jaeseoung Park, Eui-Sang Yu, Jong-Pil Im, Sun Kyu Jung, Min-A Park, Jin Ha Kim, Subin Heo, Song Lee, and Dongwoo Suh (ETRI, Korea)

**[WeB1-4]**

**10:15-10:35**

**A Low Gate-to-Drain Charge of 1.2 kV SiC DMOSFETs Utilizing a H-Shaped Poly-Si Gate**

Dusan Baek, Hyowon Yoon (Pusan Nat'l Univ., Korea), Sangyeob Kim, Gyuhyeok Kang (Kumoh Nat'l Inst. of Tech., Korea), Sumin Park, and Ogyun Seok (Pusan Nat'l Univ., Korea)